



## **AIGaInP Laser Diode**

#### Overview

DL-3038-023 is 635 nm (Typ.) AlGaInP laser diode with low threshold current. The low threshold current and short wavelength are achieved by use of a strained multiple quantum well active layer. The lasing wavelength is 635 nm which is 8 times brighter than 670 nm lasers. DL-3038-023 is suitable for battery powered laser pointers due to its low operating current and voltage.

#### **Features**

• Short wavelength : 635 nm (Typ.) • Low threshold current : Ith = 20 mA (Typ.): 3 mW CW • Output power • Low operating voltage : Vop = 2.2 V (Typ.)

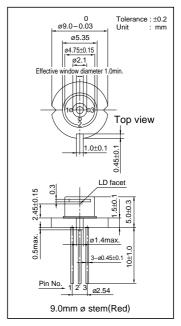
## **Absolute Maximum Ratings at Tc=°C**

Parameter		Symbol	Ratings	Unit	
Light Output		Po	3	mW	
Reverse Voltage	Laser PIN	VR	2 30	V	
Operating Temperature		Topr	-10 to +40	°C	
Storage Temperature		Tstg	-40 to +85	°C	

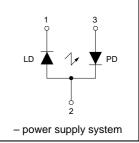
Electrical and Optical Characteristics at Tc=25°C							– power supply syster	
Parameter		Symbol	Condition	Min.	Тур.	Max.	Unit	
Threshold	Current	Ith	CW	-	20	40	mA	
Operating	Current	Iop	Po=3mW	-	25	45	mA	
Operating	Voltage	Vop	Po=3mW	-	2.2	2.4	V	
Lasing Wavelength		λp	Po=3mW	-	635	640	nm	
Beam *)	Perpendicular	$ heta oldsymbol{\perp}$	Po=3mW	25	35	40	deg.	
Divergence	Parallel	heta //	Po=3mW	6	8	10	deg.	
Off Axis	Perpendicular	$\Delta  heta  oldsymbol{\perp}$	-	-	-	±3	deg.	
Angle	Parallel	$\Delta  heta$ //	-	-	-	±3	deg.	
Differential	Efficiency	dPo/dIop	-	-	0.5	-	mW/mA	
Monitoring Output Current		Im	Po=3mW	0.1	0.2	0.6	mA	
Astigmatism		As	Po=3mW	-	8	-	μm	

#### \*) Full angle at half maximum note: The above product specifications are subject to change without notice.

### **Package Dimensions**

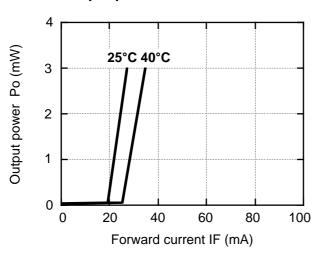


#### **Electrical Connection**

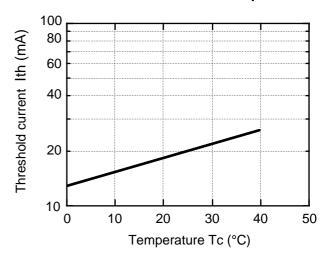


#### **Characteristics**

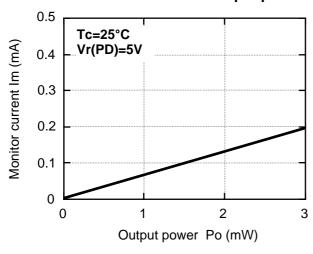
#### Output power vs. Forward current



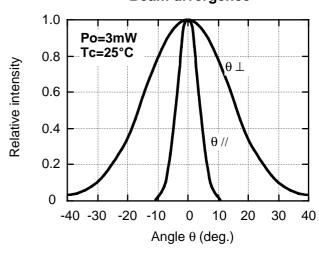
#### Threshold current vs. Temperature



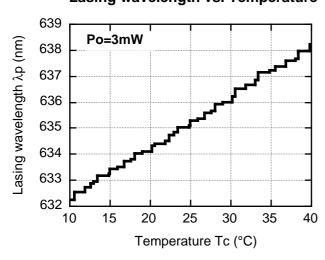
Monitor current vs. Output power



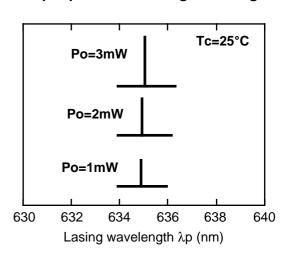
Beam divergence



#### Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



Relative intensity



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# Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

Manufactured by; Tottori SANYO Electric Co., Ltd.

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